

FAST SWITCHING SILICON PIN DIODE

DESCRIPTION:

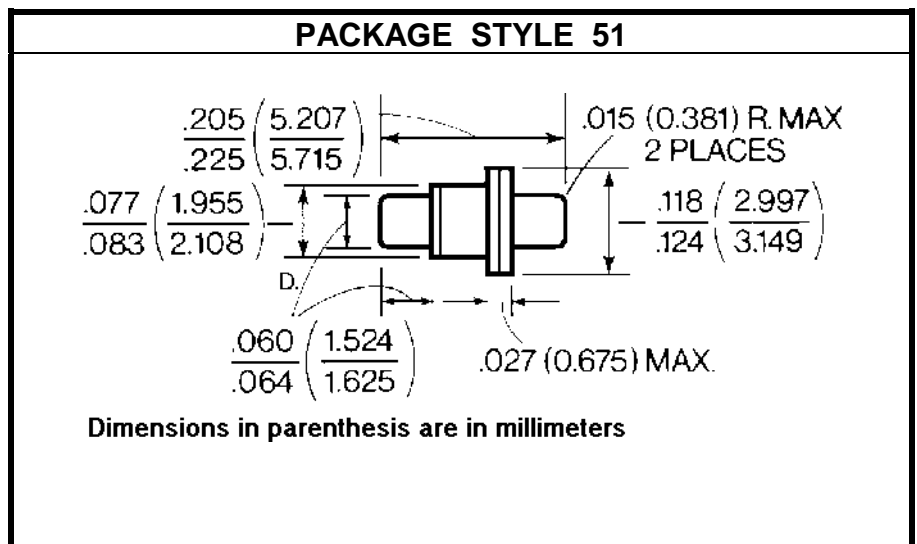
The **ASI 5082-3306** is a passivated silicon PIN diode of mesa construction. Designed for controlling and processing microwave signals up to Ku band.

FEATURES:

- 50 W Peak Pulse Power
- Switching time < 5 nS
- Heat Sink Cathode

MAXIMUM RATINGS

| | |
|-------------------------|---------------------------------|
| P_{DISS} | 0.25 W @ T _C = 25 °C |
| T_J | -65 °C to +150 °C |
| T_{STG} | -65 °C to +150 °C |


CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-----------------|---|---------|---------|---------|-------|
| V _B | I _R = 10 μA | 70 | | | V |
| C _T | V _R = 20 V f = 1.0 MHz | | | 0.45 | pF |
| R _S | I _F = 20 mA f = 100 MHz | | | 1.0 | Ω |
| t _{rr} | I _F = 20 mA V _R = 10 V | | | 10 | nS |